

TM120P03D

P-Channel Enhancement Mosfet

General Description

- Low $R_{DS(ON)}$
- RoHS and Halogen-Free Compliant

Applications

- Load switch
- PWM

General Features

$V_{DS} = -30V$ $I_D = -120A$

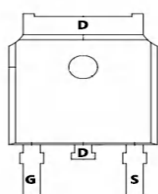
$R_{DS(ON)} = 3.0 m\Omega$ (typ.) @ $V_{GS} = -10V$

100% UIS Tested

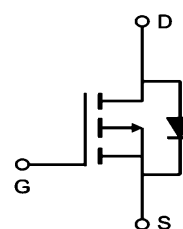
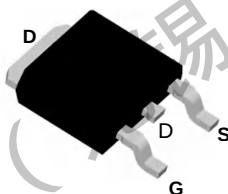
100% R_g Tested



D:TO-252-3L



Marking: 120P03



Absolute Maximum Ratings ($T_C = 25^\circ C$ Unless Otherwise Noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-30	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ -10V$	-120	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ -10V$	-78	A
I_{DM}	Pulsed Drain Current	-445	A
EAS	Single Pulse Avalanche Energy	580	mJ
IAS	Avalanche Current	80	A
$P_D @ T_C = 25^\circ C$	Total Power Dissipation	100	W
T_{STG}	Storage Temperature Range	-55 to 175	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 175	$^\circ C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient	---	62	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case	---	6.6	$^\circ C/W$

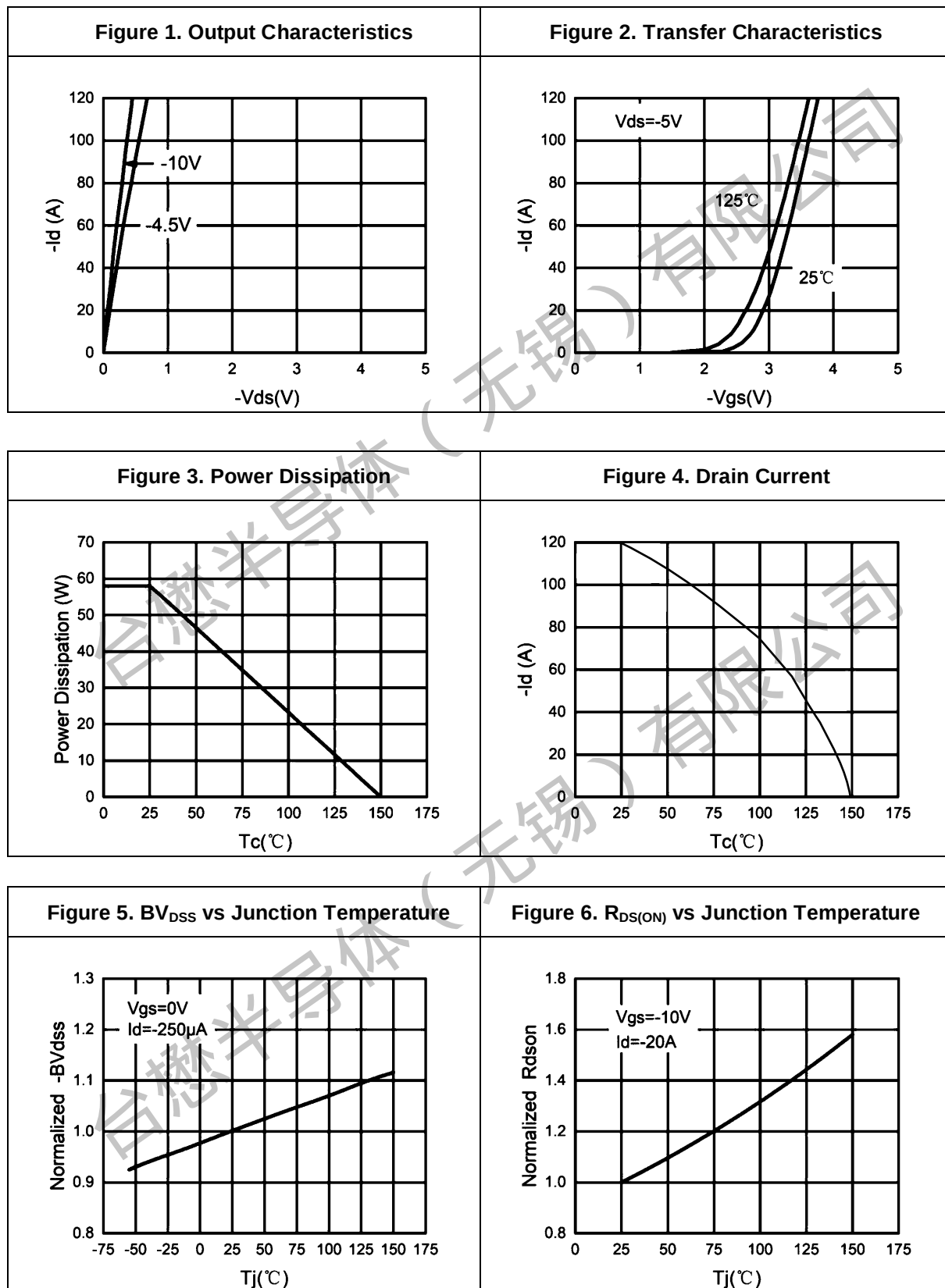
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Electrical Characteristics ($T_J=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
On/Off States						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V I _D =-250μA	-30			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-30V, V _{GS} =0V			-1	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±20V, V _{DS} =0V			±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250μA	-1	-1.5	-2.0	V
g _{FS}	Forward Transconductance	V _{DS} =-5V, I _D =-20A		65		S
R _{DS(ON)}	Drain-Source On-State Resistance	V _{GS} =-10V, I _D =-20A		3.0	4.5	mΩ
		V _{GS} =-4.5V, I _D =-20A		4.4	5.5	mΩ
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =-15V, V _{GS} =0V, f=1.0MHz		6500		pF
C _{oss}	Output Capacitance			820		pF
C _{rss}	Reverse Transfer Capacitance			540		pF
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1.0MHz		2.2		Ω
Switching Parameters						
t _{d(on)}	Turn-on Delay Time	V _{GS} =-10V, V _{DS} =-15V, R _L =0.75Ω, R _{GEN} =3Ω		14		nS
t _r	Turn-on Rise Time			13		nS
t _{d(off)}	Turn-Off Delay Time			65		nS
t _f	Turn-Off Fall Time			37		nS
Q _g	Total Gate Charge	V _{GS} =-10V, V _{DS} =-15V, I _D =-20A		130		nC
Q _{gs}	Gate-Source Charge			12		nC
Q _{gd}	Gate-Drain Charge			31		nC
Source-Drain Diode Characteristics						
I _{SD}	Source-Drain Current (Body Diode)				-120	A
V _{SD}	Forward on Voltage ^(Note 3)	V _{GS} =0V, I _S =-20A			-1.2	V
t _{rr}	Reverse Recovery Time	I _F =-20A, di/dt=100A/μs		30		ns
Q _{rr}	Reverse Recovery Charge	I _F =-20A, di/dt=100A/μs		40		nC

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Typical Electrical And Thermal Characteristics (Curves)



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Figure 7. Gate Charge Waveforms

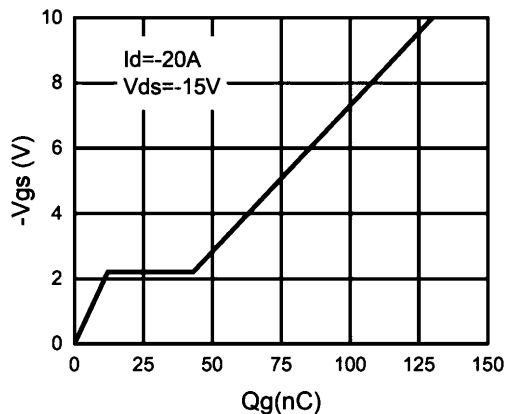


Figure 8. Capacitance

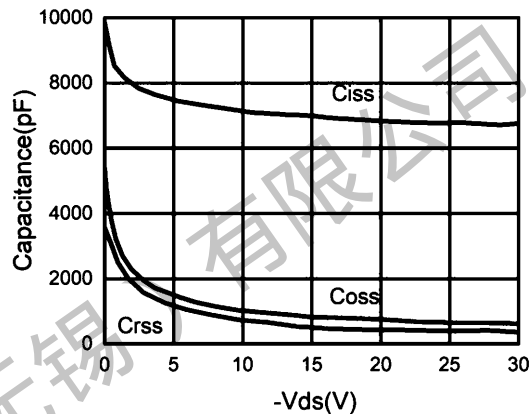


Figure 9. Body-Diode Characteristics

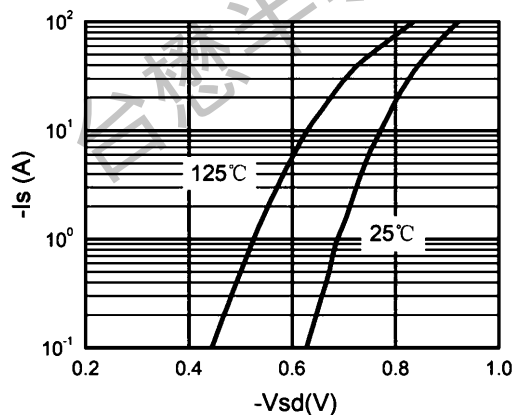
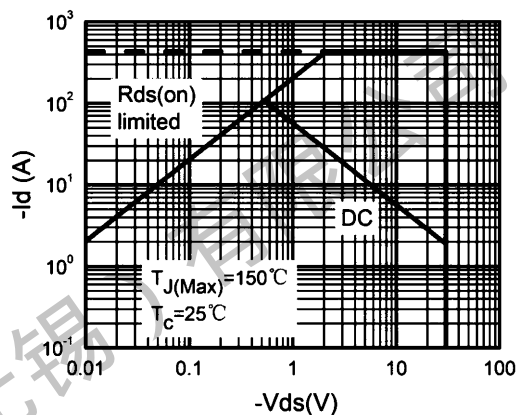


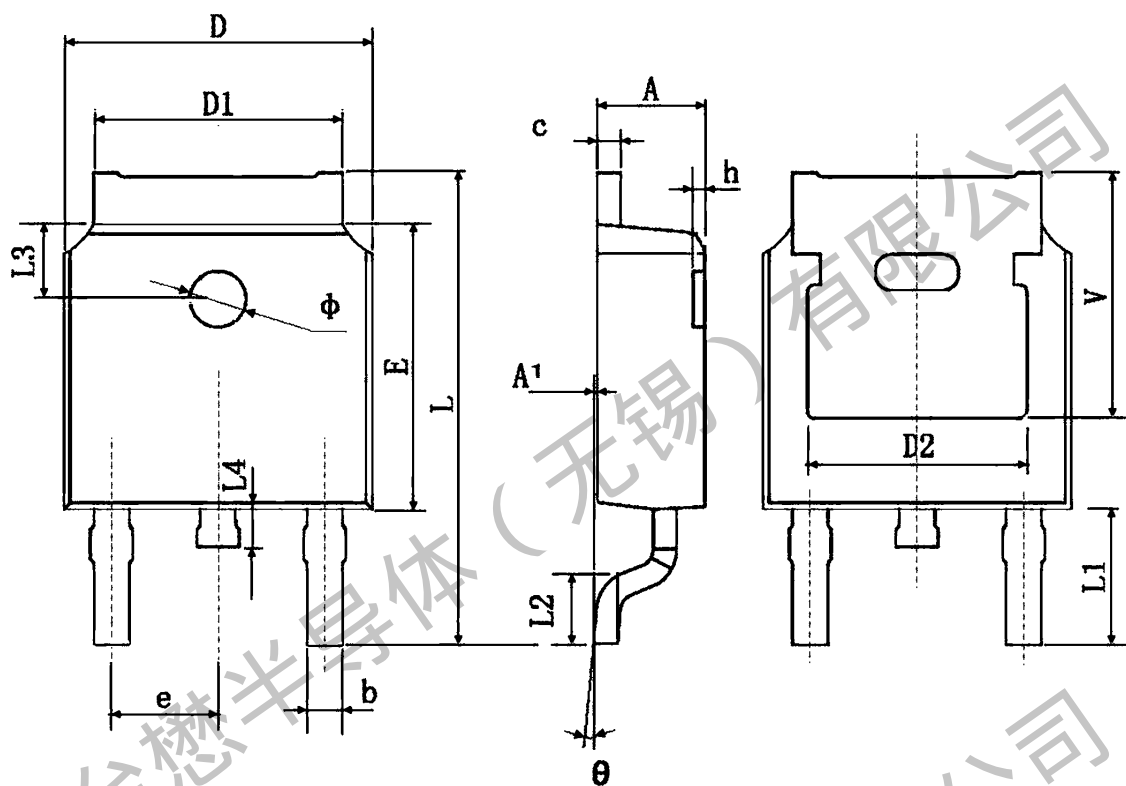
Figure 10. Maximum Safe Operating Area



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Package Mechanical Data: TO-252-3L



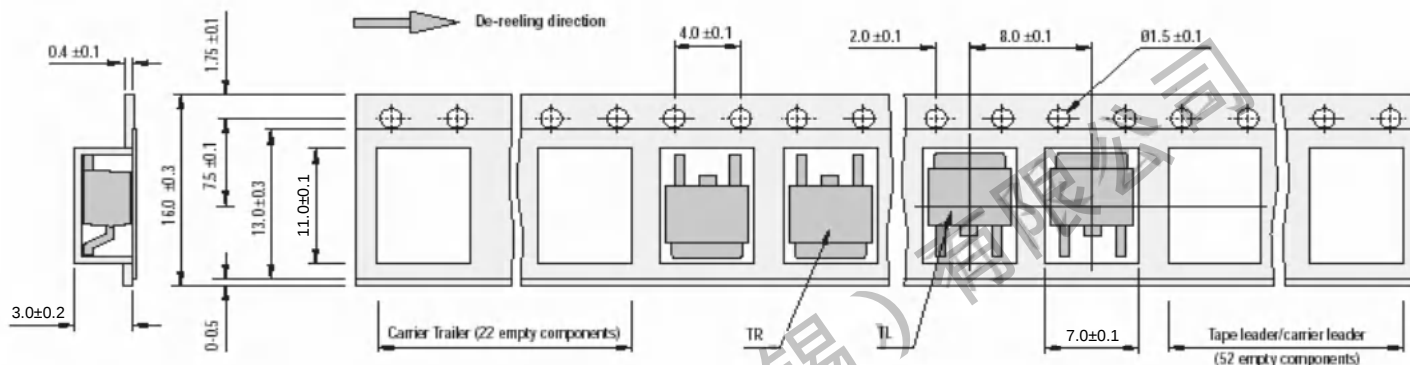
Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 TYP.		0.190 TYP.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 TYP.		0.114 TYP.	
L2	1.400	1.700	0.055	0.067
L3	1.600 TYP.		0.063 TYP.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 TYP.		0.211 TYP.	



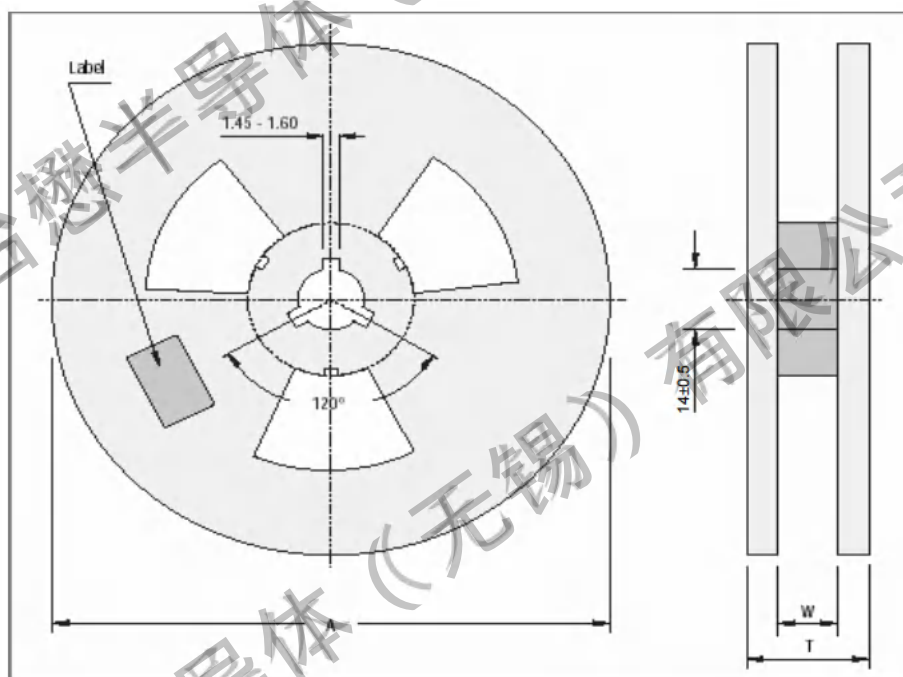
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TO-252-3L Embossed Carrier Tape



TO-252-3L Reel



All Dimensions are in mm.

Reel Specifications				
Package	Tape Width	Reel Dia. A - Max	Inside Thickness W	Reel Thickness T - max
TO-252-3L	16	330	18.0 ± 1.5	20

Packaging Information

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
2,500 pcs	13 inch	5,000 pcs	355×370×50	25,000 pcs	380×275×380	

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Revision history:

Date	Rev	Description	Page
2023.04.09	23.04	Original	